GTM

CORPORATION ISSUED DATE :2005/12/20 REVISED DATE :

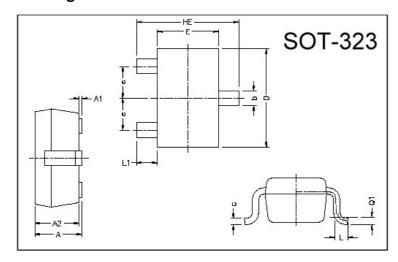
GS420SD

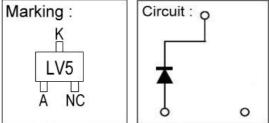
SURFACE MOUNT, SCHOTTKY BARRIER DIODE **VOLTAGE 40V, CURRENT 0.1A**

Description

The GS420SD is designed for low power rectification.

Package Dimensions





REF.	Milli	meter	REF.	Millimeter				
	Min.	Max.	nLI.	Min.	Max.			
Α	0.80	1.10	L1	0.42 REF.				
A1	0	0.10	L	0.15	0.35			
A2	0.80	1.00	b	0.25	0.40			
D	1.80	2.20	С	0.10	0.25			
Е	1.15	1.35	е	0.65 REF.				
HE	1.80	2.40	Q1	0.15 BSC.				

Absolute Maximum Ratings at TA = 25° C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+125	$^{\circ}$
Storage Temperature	Tstg	-40 ~ +125	$^{\circ}$
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	40	V
Maximum RMS Voltage	V_{RMS}	28	V
Maximum DC Blocking Voltage	V_{DC}	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	1.0	A
Typical Junction Capacitance between Terminal (Note 1)	CJ	6.0	pF
Maximum Average Forward Rectified Current	lo	0.1	A
Total Power Dissipation	PD	225	mW

Electrical Characteristics (at TA = 25°C unless otherwise noted)

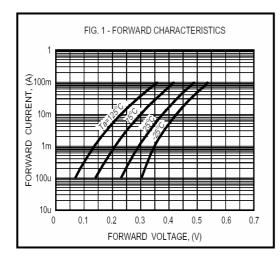
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)R	40	-	-	٧	IR=100μA
Maximum Instantaneous Forward Voltage	VF	-	-	450	mV	IF=10mA
Maximum Average Reverse Current	lr	-	-	1.0	uA	VR=10V

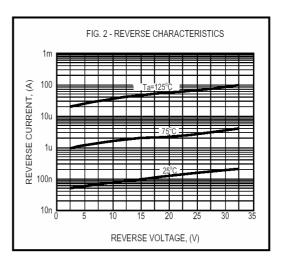
Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10 volts.

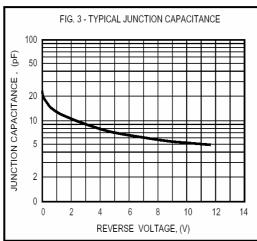
2. ESD sensitive product handling required.

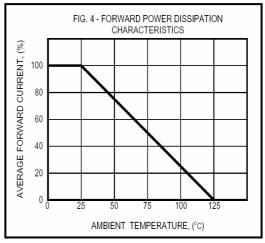
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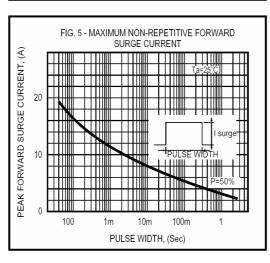
Characteristics Curve











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